

Data sheet acquired from Harris Semiconductor SCHS026

CMOS Quad Bilateral Switch

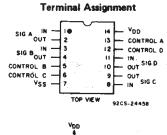
For Transmission or Multiplexing of Analog or Digital Signals

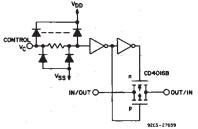
High-Voltage Types (20-Volt Rating)

■ CD4016B Series types are quad bilateral switches intended for the transmission or multiplexing of analog or digital signals. Each of the four independent bilateral switches has a single control signal input which simultaneously biases both the p and n device in a given switch on or off.

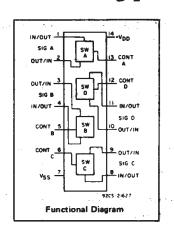
The CD4016 "B" Series types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

CD4016B Types





Schematic diagram - 1 of 4 identical sections.



Features:

- 20-V digital or ± 10-V peak-to-peak switching
- \blacksquare 280- Ω typical on-state resistance for 15-V operation
- Switch on-state resistance matched to within 10 Ω typ. over 15-V signal-input range
- High on/off output-voltage ratio: 65 dB typ. @ f_{is} = 10 kHz, R_L = 10 k Ω
- High degree of linearity: <0.5% distortion typ. @ f_{is} = 1 kHz, V_{is} = 5 V_{p-p} , V_{DD} - V_{SS} \geqslant 10 V, R L = 10 k Ω
- Extremely low off-state switch leakage resulting in very low offset current and high effective off-state resistance:
 100 pA typ. @ VDD-VSS=18 V, TA=25°C
- \blacksquare Extremely high control input impedance (control circuit isolated from signal circuit: 1012 Ω typ.
- Low crosstalk between switches:
 -50 dB typ. @ f_{is} = 0.9 MHz, R_L = 1 kΩ
- Matched control-input to signal-output capacitance:
 - Reduces output signal transients
- Frequency response, switch on = 40 MHz
- 100% tested for quiescent current at 20 V
- Maximum control input current of 1 μA
 at 18 V over full package temperature range; 100 nA at 18 V at 25°C
- 5-V, 10-V, and 15-V parametric ratings Applications:
- Analog signal switching/multiplexing
 Signal gating
 Modulator
 Squelch control
 Demodulator
 Chopper
 Commutating switch
- Digital signal switching/multiplexing
- CMOS logic implementation
- Analog-to-digital & digital-toanalog conversion
- Digital control of frequency, impedance, phase, and analog-signal gain

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following range:

CHARACTERISTIC	LIN	UNITS	
- CHAILAGT ETTIGITG	Min.	Max.	0.41.3
Supply Voltage Range (For T _A = Full Package Temperature Range)	3	18	٧

MAXIMUM RATINGS, Absolute-Maximum Values:

PLY-VOLTAGE RANGE, (V _{DD})		SUPPLY-VOLTAGE RANGE, (V _{DD})
es referenced to V _{SS} Terminal)		bitages referenced to VSS Terminal)
OLTAGE RANGE, ALL INPUTS0.5V to V _{DD} +0.	0.5V to	UT VOLTAGE RANGE, ALL INPUTS
JT CURRENT, ANY ONE INPUT±10r		INPUT CURRENT, ANY ONE INPUT
DISSIPATION PER PACKAGE (PD):		WER DISSIPATION PER PACKAGE (PD):
\= -55°C to +100°C500m		or T _A = -55°C to +100°C
x = +100°C to +125°C Derate Linearity at 12mW/°C to 200m	Derate Linearity at 12mW/O(or T _A = +100°C to +125°C
DISSIPATION PER OUTPUT TRANSISTOR	R	ICE DISSIPATION PER OUTPUT TRANS
A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	NGE (All Package Types)	OR $T_A = FULL PACKAGE-TEMPERATUR$
TING-TEMPERATURE RANGE (TA)55°C to +125	55°C	RATING-TEMPERATURE RANGE (TA)
GE TEMPERATURE RANGE (T _{stg})65°C to +150	65°C	RAGE TEMPERATURE RANGE (Tstg)
EMPERATURE (DURING SOLDERING):	\$	D TEMPERATURE (DURING SOLDERIN
ence 1/16 + 1/32 inch /1 59 + 0.79mm\ from case for 10e may +265	om case for 10e may	distance 1/16 + 1/32 inch /1 59 + 0 79m

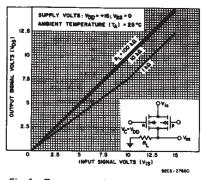


Fig. 1— Typ. on-state characteristics for 1 of 4 switches with $V_{DD} = +15 \text{ V}$, $V_{SS} = 0 \text{ V}$.

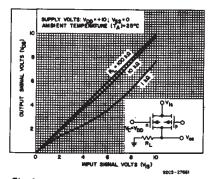


Fig. 2— Typ. on-state characteristics for 1 of 4 switches with V_{DD} = +10 V, V_{SS} = 0 V.

ELECTRICAL CHARACTERISTICS

		<u> </u>									·
CHARACTERISTIC	TI	TEST CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)					UNITS	
e di esta. Ne	V _{IN} (V)			V _{DD}			ŕ			+25 Typ. Max.	
				(V)	-55	-55 -40		+85 +125			
			0,5	5	0.25	0.25	7.5	7.5	0.01	0.25	
Quiescent Device Current, IDD		•	0,10	10	0.5	0.5	15	_	0.01	0.5	μА
,	:		0,15	15	1	1	30	<u> </u>	0.01	1	
Signal Inputs (Vis	and Output	(V _{OS})	0,20	20	5	5	150	150	0.02	5	<u></u>
							-		Γ	Г	<u> </u>
On-State Resistance, r _{on}	V _C = V _{DD} R _L = 10kΩ	V _{is} =V _{DD} or	VSS	10	600	610	840	960		660	
Max.	Returned	V _{is} =4.75 to	5.75 V	10	1870	1900	2380	2600	-	2000	
₹		V _{is} =V _{DD} or		15	360	370	520	600		400	Ω
40.6	2	V _{is} =7.25 to	7.75 V	15	775	790	1080	1230		850	
∆On-State Resistance						-			15		·
Between Any	$R_L = 10 \text{ k}\Omega$, $V_C = V_{DD}$					-			10		Ω
2 Switches, ∆ron					-	_	-	- 1	5		
Total Harmonic Distortion, THD	= 5V (Sine v R _L =10 kΩ,	$V_C = V_{DD} = 5 \text{ V}, V_{SS} = -5 \text{ V}, V_{is}$ = 5 V (Sine wave centered on 0' $R_L = 10 \text{ k}\Omega, f_{is} = 1 \text{ kHz sine wave}$					_	1	0.4	-	%
-3dB Cutoff Frequency (Switch on)	$V_{is(p-p)} = 5$	5 V, VSS=-5 V (Sine wav 1 0 V) RL=	е		. -	-	1	_	40	_ :	MHz
-50dB Feed- through Frequency (Switch off)	V _C =V _{SS} = - (Sine wave of R _L = 1 lkΩ	-5V, V _{is(p-p} centered on ()=5V 0V)		-	-		_	1.25	_	MHz
Input/Output Leakage Current (Switch off) I _{is} Max.	$V_{C} = 0 V$ $V_{is} = 18 V$, $V_{is} = 0 V$, $V_{os} = 18 V$			18	±0.1	±0.1	±1	±1 .	10-4	±0.1	μΑ
-50 dB Crosstalk Frequency	V _C (B) = V _S V _{is} (A) = 5 \	$V_C(A) = V_{DD} = +5 V$, $V_C(B) = V_{SS} = -5 V$, $V_{is}(A) = 5 V_{p-p}$, 50Ω source $R_1 = 1 k\Omega$							0.9	-,	MHz
Propagation	RL = 200 ks			5	_	_	_	-	40	100	
Delay (Signal	VC = Vpp, CL = 50 pF	V _{SS} = GND,		10	_	-	_	_	20		ns
Input to Signal Output) t _{pd}	V _{is} = Square Wave 0 to V _D D t _r , t _f = 20 ns				-	_	_	-	15	30	
Capacitance: Input, C _{is}	V _{DD} = +5 V					_	_	_	4		
Output, C _{OS}	VC = VSS =				-	-	-	-	4	-	pF
Feedthrough, C _{ios}					_	-	-	-	0.2	-	

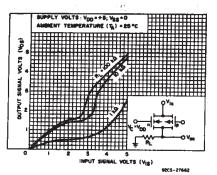


Fig. 3—Typ. on-state characteristics for 1 of 4 switches with V_{DD} = +5 V, V_{SS} = 0 V.

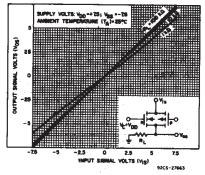


Fig. 4—Typ. on-state characteristics for 1 of 4 switches with V_{DD} = +7.5 V, V_{SS} =-7.5 V.

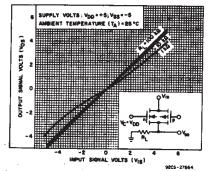


Fig. 5— Typ. on-state characteristics for 1 of 4 switches with V_{DD} =+5 V, V_{SS} *-5 V.

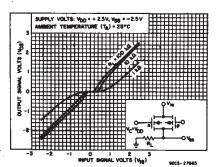


Fig. 6—Typ. on-state characteristics for 1 of 4 switches with V_{DD} = +2.5 V, V_{SS} = -2.5 V.

ELECTRICAL C	HARACTERISTICS (cont'd)								
CHARACTERISTIC	TEST CONDITIONS	LIMITS AT INDICATED TEMPERATURES (°C)						UNIT	
		V _{DD}	<u> </u>	T	l	· ·	+25		S
		(V)	-55	-40	+85	+125	Тур.	Max.	
Control (V _C)									
Control Input Low Voltage, VILC (Max.)	$ H_{is} < 10 \mu A$ $ V_{is} = V_{SS} $ $ V_{SS} = V_{DD} $ $ V_{SS} = V_{DD} $	5,10, 15	0.9	0.9	0.4	0.4	-	0.7	٧
Control Input		5	3.5 (Min.)						
High Voltage,	See Fig. 10	10	7 (Min.)						
VIHC	t in the second	15 . 11 (Min.)							
Input Current, IN (Max.)	V _{is} ≤ V _{DD} V _{DD} - V _{SS} = 18 V V _{CC} ≤ V _{DD} - V _{SS}	18	±0.1	±0.1	±1	±1	±10-5	±0.1	μΑ
Crosstalk (Con- trol Input to Signal Output)	$V_C = 10 \text{ V (Sq. Wave)}$ t_r , $t_f = 20 \text{ ns}$ $R_L = 10 \text{ k}\Omega$	10	_	_	-	_	50	_	mV
Turn-On	t _r , t _f = 20 ns	5	_	-	_	_	35	70	
Propagation	CL = 50 pF	10	_	_	_	_	20	40	ns
Delay	R _L = 1 kΩ	15	_	-	_	_	15	30	
Maximum Control Input Repetition Rate	$\begin{aligned} &V_{is} = V_{DD}, V_{SS} = GND, \\ &R_{L} = 1 \text{ k}\Omega \text{ to gnd,} \\ &C_{L} = 50 \text{ pf,} \\ &V_{C} = 10 \text{ V(Square} \\ &\text{wave centered on 5 V)} \\ &t_{r}, t_{f} = 20 \text{ ns,} \\ &V_{OS} = \frac{1}{2} V_{OS} @ 1 \text{ kHz} \end{aligned}$	10	1	_ :	-	_	10	-	MHz
Input Capacitance, C _{IN}	-		-	_	-	_	5	7.5	μF

	Switch Input								Switch Output		
VDD	Vis	V _{os} (V)									
(V)	(V)	–55°C	-40°C	25°C*	25°C▲	+85°C	+125°C	Min.	Max.		
5	0	0.25	0.2	0.2	0.16	0.12	0.14	_	0.4		
5	5	-0.25	-0.2	-0.2	-0.16	-0.12	-0.14	4.6	_		
10	0	0.62	0.5	0.5	0.4	0.3	0.35	_	0.5		
10	10	-0.62	-0.5	-0.5	-0.4	-0.3	-0.35	9.5	-		
15	0	1.8	1.4	1.5	1.2	1	1.1	_	1.5		
15	15	-1.8	-1,4	-1.5	-1.2	-1	-1.1	13.5	_		

^{*} Plastic package

Ceramic package

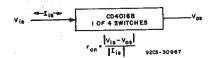


Fig. 10— Determination of r_{on} as a test condition for control input high voltage (V_{IHC}) specification.

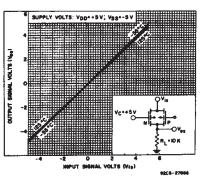


Fig. 7.— Typ. on-state characteristics as a function of temp. for 1 of 4 switches with V_{DD} = +5 V, V_{SS} = -5 V.

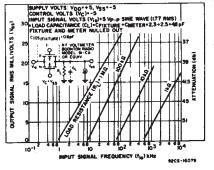


Fig. 8 - Typ. feedthru vs. frequency - switch off.

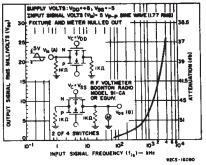


Fig. 9— Typical crosstalk between switch circuits in the same package.

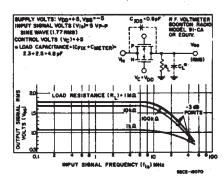
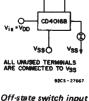


Fig. 11 — Typical frequency response — switch on.

TYPICAL ON-STATE RESISTANCE CHARACTERISTICS, TA = 25°C

CHARAC- TERISTIC*	SUP COND	PLY ITIONS						
				R _L = 1kΩ		R _L = 10kΩ		100kΩ
	V _{DD} (V)	V _{SS}	(SS)	V _{is} (V)	VALUE:	(V)	VALUE (Ω)	V _{is} (V)
_	+15	0	200	+15	200	+15	180	+15
ron		Ľ	200	0	200	0	200	0
ron (max.)	+15	0	300	+11	300	+9.3	320	+9.2
	+10	0	290	+10	250	+10	240	+10
ron	.,0		290	0	250	0	300	0
r _{on} (max.)	+10	0	500	+7.4	560	+5.6	610	+5.5
	+ 5	0	860	+ 5	470	+ 5	450	+ 5
ron			600	0	. 580	0	800	0
ron (max.)	+ 5	0	1.7k	+4.2	7k	+2.9	33k	+2.7
	+7.5		200	+7.5	200	+7.5	180	+7.5
ron			200	-7.5	200	7.5	180	-7.5
ron (max.)	+7.5	-7.5	290	±0.25	280	±25	400	±0.25
r.	+ 5	- 5	260	+ 5	250	+ 5	240	+ 5
ron		, - 3	310	- 5	250	- 5	240	– 5
ron (max.)	+ 5	- 5	600	±0.25	580	±0.25	760	±0.25
r	+2.5	5 -2.5	590	+2.5	450	+2.5	490	+2.5
ron			720	-2.5	520	-2.5	520	-2.5
ron (max.)	+2.5	-2.5	232k	±0.25	300k	±0.25	870k	±0.25

^{*} Variation from aperfect switch, $r_{on} = 0 \Omega$.



OVD0

Fig. 12 - Off-state switch input or output leakage current test circuit.

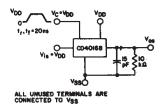
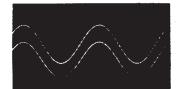


Fig. 13 — Test circuit for square-wave response.



SCALE: $X = 0.2 \text{ ms/DIV } Y = 2.0 \text{ V/DIV } VDD = VC = +7.5V, VSS = .7.5V, RL = 10K\Omega$ CL = 15 pF | 15 = 1 KHz VIS = 5V pp | DISTORTION = 0.2 %

92CS-27612

Fig. 14 – Typical sine wave response of V_{DD} = +7.5 V, V_{SS} = -7.5 V.



SCALE: X = 0.2 ms/DIV Y = 2.0 V/DIV VDD = VC = +5 V. VSS = 5 V. R_L = 10KΩ C_L = 15 pF I_S = 1 KHz. V_{IS} = 5 V p p DISTORTION = 0.4 %

9205-27613

Fig. 15 – Typical sine wave response of V_{DD} = +5 V, V_{SS} = -5 V.



SCALE: X = 0.2 ms/DIV Y = 2.0 V/DIV $V_{DD} = V_{C} = *2.5 \text{V}$, $V_{SS} = *2.5 \text{V}$, $R_{L} = 10 \text{K}\Omega$ $C_{L} = 15 \text{ pf}$ $I_{IS} = 1 \text{ KHz}$ $V_{IS} = 5 \text{V pp}$ DISTORTION = 3 %

92CS - 27614

Fig. 16 — Typical sine wave response of V_{DD} = +2.5 V, V_{SS} = -2.5 V.



SCALE: X = 100 ns/DIV Y = 5.0 V/DIV

92CS-276I5

Fig.17 - Typical square wave response at $V_{DD} = V_C = +15 V$, $V_{SS} = Gnd$.



SCALE: X = 100 ns/DIV Y = 5.0 V/DIV

9205-27616

Fig.18 — Typical square wave response at $V_{DD} = V_C = +10 \text{ V}$, $V_{SS} = \text{Gnd}$.



SCALE: X = 100 ns/DIV

9205-27617

Fig.19 – Typical square wave response at V_{DD} = V_C = +5 V, V_{SS} = Gnd.

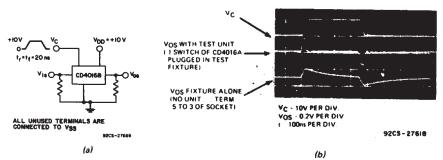


Fig. 20 - Crosstalk-control input to signal output.

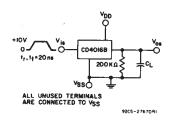


Fig. 21 — Propagation delay time signal input (V_{IS}) to signal output (V_{OS}) .

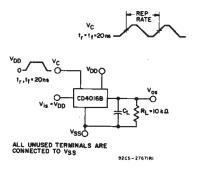


Fig. 22 - Max. control-input repetition rate.

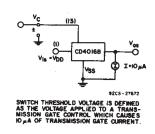


Fig.23 - Switch threshold voltage.

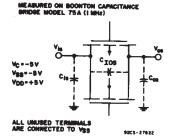
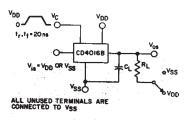


Fig.24 — Capacitance C_{IOS} and C_{OS} .



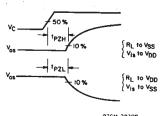
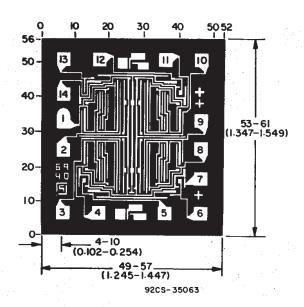


Fig.25 - Turn-On propagation delay-control input.

Dimensions and pad layout for CD4016BH



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch) .

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